

SINGLE REACTOR, MULTI-PRESSURE CHEMICAL VAPOR DEPOSITION FOR SEMICONDUCTOR DEVICES

Abstract of the Disclosure

An apparatus and method for forming at least a portion of an electronic device include a High Vacuum–Chemical Vapor Deposition (UHV–CVD) system and a Low Pressure–Chemical Vapor Deposition (LPCVD) system using a common reactor. The invention overcomes the problem of silicon containing wafers being dipped in HF acid prior to CVD processing, and the problem of surface passivation between processes in multiple CVD reactors.

Figures